

Si550

PRELIMINARY DATA SHEET

VOLTAGE-CONTROLLED CRYSTAL OSCILLATOR (VCXO) 10 MHz to 1.4 GHz

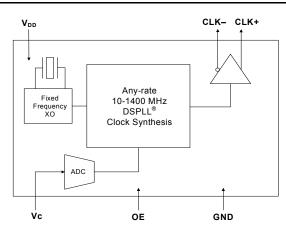
Features

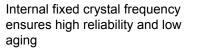
- Available with any-rate output frequencies from 10 MHz to 945 MHz and selected frequencies to 1.4 GHz
- 3rd generation DSPLL[®] with superior jitter performance
- 3x better frequency stability than SAW based oscillators
- Applications
- SONET / SDH
- xDSL
- 10 GbE LAN / WAN
- Optical modulesClock and data recovery

Description

The Si550 VCXO utilizes Silicon Laboratories' advanced DSPLL[®] circuitry to provide a low-jitter clock at high frequencies. The Si550 is available with any-rate output frequency from 10 to 945 MHz and selected frequencies to 1400 MHz. Unlike traditional VCXO's where a different crystal is required for each output frequency, the Si550 uses one fixed crystal to provide a wide range of output frequencies. This IC based approach allows the crystal resonator to provide exceptional frequency stability and reliability. In addition, DSPLL clock synthesis provides superior supply noise rejection, simplifying the task of generating low-jitter clocks in noisy environments typically found in communication systems. The Si550 IC-based VCXO is factory configurable for a wide variety of user specifications, including frequency, supply voltage, output format, tuning slope, and temperature stability. Specific configurations are factory programmed at time of shipment, thereby eliminating long lead times associated with custom oscillators.

Functional Block Diagram





- Available CMOS, LVPECL, LVDS, & CML outputs
- 3.3, 2.5, and 1.8 V supply options
- Industry-standard 5 x 7 mm package and pinout
- Lead-free/RoHS-compliant

Low-jitter clock generation

See page 8. Pin Assignments: See page 7. (Top View) Vc 1 6 V_{DD} OE 2 5 CLK-GND 3 4 CLK+

Ordering Information:

Si550

1. Electrical Specifications

Table 1. Recommended Operating Conditions

Symbol	Test Condition	Min	Тур	Мах	Units
V _{DD}	3.3 V option	2.97	3.3	3.63	
	2.5 V option	2.25	2.5	2.75	V
	1.8 V option	1.71	1.8	1.89	-
I _{DD}	Output enabled	_	90		m 4
	TriState mode		60		mA
	V _{IH}	0.75 x V _{DD}	_	—	N
	V _{IL}	—		0.5	
T _A		-40	_	85	°C
	V _{DD}	V _{DD} 3.3 V option 2.5 V option 1.8 V option I _{DD} Output enabled TriState mode V _{IH} V _{IL}	V _{DD} 3.3 V option 2.97 2.5 V option 2.25 1.8 V option 1.71 I _{DD} Output enabled — TriState mode — V _{IH} 0.75 x V _{DD}	$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	V _{DD} 3.3 V option 2.97 3.3 3.63 2.5 V option 2.25 2.5 2.75 1.8 V option 1.71 1.8 1.89 IDD Output enabled — 90 — TriState mode — 60 — V _{IH} 0.75 x V _{DD} — — V _{IL} — — 0.5

Notes:

1. Selectable parameter specified by part number. See Section 3. "Ordering Information" on page 8 for further details.

2. OE pin includes a 17 k Ω pullup resistor to VDD. Pulling OE to ground causes outputs to tristate.

Table 2. V _C Control Voltage Inp	ut
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Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Control Voltage Tuning Slope ^{1,2,3}	κ _v	10 to 90% of V _{DD}	_	45 90 135 180		ppm/V
Control Voltage Linearity ⁴	L _{VC}	BSL	-5	±1	+5	%
		Incremental	-10	±5	+10	/0
Modulation Bandwidth	BW		9.3	10.0	10.7	kHz
V _C Input Impedance	Z _{VC}		500	_	—	kΩ
Nominal Control Voltage	V _{CNOM}	@ f _O	_	3/8 x V _{DD}		V
Control Voltage Tuning Range	V _C		0		V_{DD}	V

Notes:

1. Positive slope; selectable option by part number. See Section 3. "Ordering Information" on page 8.

For best jitter and phase noise performance, always choose the smallest K_V that meets the application's minimum APR requirements. See "AN266: VCXO Tuning Slope (K_V), Stability, and Absolute Pull Range (APR)" for more information.
 K variation is +28% of two calls always choose the smallest K_V that meets the application's minimum APR requirements.

3. K_V variation is ±28% of typical values.

4. BSL determined from deviation from best straight line fit with V_C ranging from 10 to 90% of V_{DD} . Incremental slope determined with V_C ranging from 10 to 90% of V_{DD} .



Table 3. CLK± Output Frequency Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Nominal Frequency ^{1,2,3}	f _O	LVDS/CML/LVPECL	10	—	945	MHz
		CMOS	10	—	160	IVITIZ
Temperature Stability ^{1,4}	Δf/f _O	T _A = -40 to +85 °C	-20 -50 -100		+20 +50 +100	ppm
Absolute Pull Range ^{1,4}	APR		±25	—	±150	ppm
Aging		Frequency drift over 15 year life.	_	—	±10	ppm
Power up Time ⁵	t _{OSC}		_	—	10	ms

Notes:

1. See Section 3. "Ordering Information" on page 8 for further details.

2. Specified at time of order by part number. Also available in frequencies from 970 to 1134 MHz and 1213 to 1417 MHz.

3. Nominal output frequency set by $V_{CNOM} = 3/8 \times V_{DD}$.

4. Selectable parameter specified by part number.

5. Time from power up or tristate mode to f_{O} .

Table 4. CLK± Output Levels and Symmetry

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
LVPECL Output Option ¹	Vo	mid-level	V _{DD} – 1.42	—	V _{DD} – 1.25	V
	V _{OD}	swing (diff)	1.1	—	1.9	V _{PP}
	V _{SE}	swing (single-ended)	0.5	—	0.93	V _{PP}
LVDS Output Option ²	Vo	mid-level	1.125	1.20	1.275	V
	V _{OD}	swing (diff)	0.32	0.40	0.50	V _{PP}
CML Output Option ²	Vo	mid-level	—	V _{DD} – 0.75	—	V
	V _{OD}	swing (diff)	0.70	0.95	1.20	V _{PP}
CMOS Output Option ³	V _{OH}	I _{OH} = 32 mA	0.8 x V _{DD}	—	V _{DD}	V
	V _{OL}	I _{OL} = 32 mA	—	—	0.4	v
Rise/Fall time (20/80%)	t _{R,} t _F	LVPECL/LVDS/CML	_	_	350	ps
		CMOS with CL = 15 pF	_	1	_	ns



Parameter	Symbol	Tes	t Condition	Min	Тур	Max	Units
Symmetry (duty cycle)	SYM	LVPECL: LVDS: CMOS:	V _{DD} – 1.3 V (diff) 1.25 V (diff) V _{DD} /2	45	_	55	%
Notes: 1. 50 Ω to V_{DD} – 2.0 V. 2. R_{term} = 100 Ω (different 3. C_L = 15 pF	ial).						

Table 5. CLK± Output Phase Jitter

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Phase Jitter (RMS) ^{1,2,3} for F _{OUT} ≥ 500 MHz	φJ	Kv = 45 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 80 MHz (OC-192)		0.35 0.38		ps
		Kv = 90 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 80 MHz (OC-192)	_	0.43 0.41		_
		Kv = 135 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 80 MHz (OC-192)	_	0.52 0.46	_	_
		Kv = 180 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 80 MHz (OC-192)	_	0.64 0.52		
Phase Jitter (RMS) ^{1,2,3} for F _{OUT} of 125 to 500 MHz	φJ	Kv = 45 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 80 MHz (OC-192)	_	0.42 0.58		ps
		Kv = 90 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 80 MHz (OC-192)	_	0.48 0.60		
		Kv = 135 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 80 MHz (OC-192)	_	0.57 0.64		
		Kv = 180 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 80 MHz (OC-192)	_	0.67 0.68		

Notes:

1. Differential Modes: LVPECL/LVDS/CML. Refer to AN255, AN256, and AN266 for further information.

2. For best jitter and phase noise performance, always choose the smallest K_V that meets the application's minimum APR requirements. See "AN266: VCXO Tuning Slope (K_V), Stability, and Absolute Pull Range (APR)" for more information.

3. See "AN255: Replacing 622 MHz VCSO devices with the Si550 VCXO" for comparison highlighting power supply rejection (PSR) advantage of Si55x versus SAW-based solutions.



Table 6. CLK± Output Period Jitter

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Period Jitter*	J _{PER}	RMS		2		ps
for F _{OUT} ≤ 160 MHz		Peak-to-Peak		14		
*Note: Any output mode, including CMOS, LVPECL, LVDS, CML. N = 1000 cycles.						

Table 7. CLK± Output Phase Noise (Typical)

Configuration	f _C K _V Output	74.25 MHz 45 ppm/V CMOS	300 MHz 90 ppm/V LVPECL	622.08 MHz 45 ppm/V LVPECL	Units
Offest Frequency (f)		£	2 (f)		
100 Hz		-94	-74	-77	
1 kHz		-117	-98	-101	
10 kHz		-128	-112	-114	dBc/Hz
100 kHz		-135	-122	-118	0.0 0/1 IZ
1 MHz		-138	-134	-128	
10 MHz		-143	-144	-144	
100 MHz		n/a	-147	-147	



Table 8. Absolute Maximum Ratings

Parameter	Symbol	Rating	Units				
Supply Voltage	V _{DD}	-0.5 to +3.8	Volts				
Input Voltage	VI	–0.5 to V _{DD} + 0.3	Volts				
Storage Temperature	Τ _S	-55 to +125	°C				
ESD Sensitivity (HBM, per JESD22-A114)	ESD	>2500	Volts				
Soldering Temperature (lead-free profile) T _{PEAK} 260 °C							
Soldering Temperature Time @ T _{PEAK} (lead-free profile) t _P 10 seconds							
Note: Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Functional operation or specification compliance is not implied at these conditions.							

Table 9. Environmental Compliance

The Si550 meets the following qualification test requirements.

Parameter	Conditions/ Test Method
Mechanical Shock	MIL-STD-883F, Method 2002.3 B
Mechanical Vibration	MIL-STD-883F, Method 2007.3 A
Solderability	MIL-STD-883F, Method 203.8
Gross & Fine Leak	MIL-STD-883F, Method 1014.7
Resistance to Solvents	MIL-STD-883F, Method 2016



2. Pin Descriptions

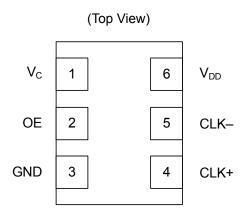


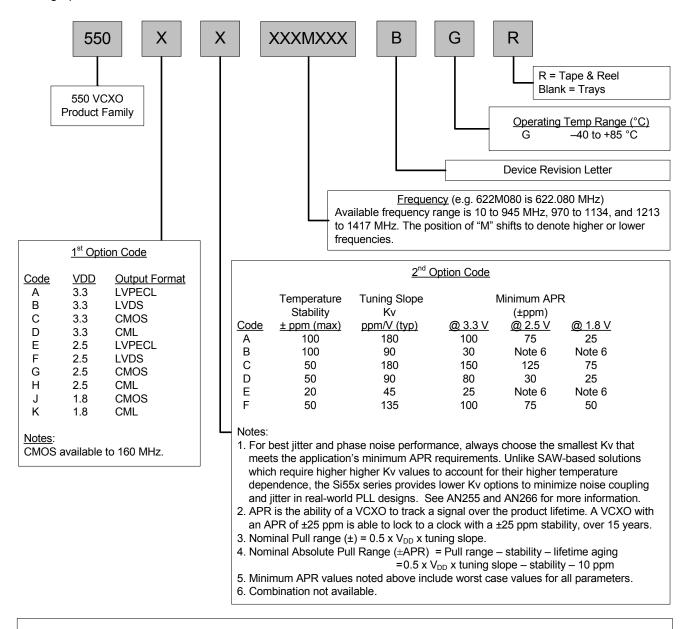
Table 10. Si550 Pin Descriptions

Pin	Name	Туре	Function		
1	V _C	Analog Input	Control Voltage		
2	OE*	Input	Output Enable: 0 = clock output disabled (outputs tri-stated) 1 = clock output enabled		
3	GND	Ground	Electrical and Case Ground		
4	CLK+	Output	Oscillator Output		
5	CLK– (N/A for CMOS)	Output	Complementary Output (N/C for CMOS)		
6	V _{DD}	Power	Power Supply Voltage		
*Note: OE	*Note: OE includes 17 k Ω pullup resistor to V _{DD} .				



3. Ordering Information

The Si550 was designed to support a variety of options including frequency, temperature stability, tuning slope, output format, and V_{DD} . Specific device configurations are programmed into the Si550 at time of shipment. Configurations are specified using the Part Number Configuration chart shown below. Silicon Labs provides a web browser-based part number configuration utility to simplify this process. Refer to www.silabs.com/VCXOPartNumber to access this tool and for further ordering instructions. The Si550 VCXO series is supplied in an industry-standard, RoHS compliant, lead-free, 6-pad, 5×7 mm package. Tape and reel packaging is an ordering option.

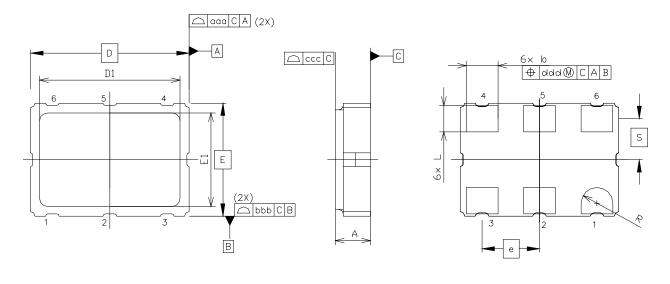


Example Part Number: 550AF622M080BGR is a 5 x 7 mm VCXO in a 6 pad package. The nominal frequency is 622.080 MHz, with a 3.3 V supply and LVPECL output. Temperature stability is specified as \pm 50 ppm and the tuning slope is 135 ppm/V. The part is specified for a -40 to +85 C° ambient temperature range operation and is shipped in tape and reel format.



4. Outline Diagram and Suggested Pad Layout

Figure 1 illustrates the package details for the Si550. Table 11 lists the values for the dimensions shown in the illustration.



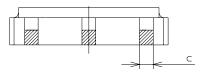


Figure 1. Si550 Outline Diagram

Dimension	Min	Nom	Max	
А	1.45	1.65	1.85	
b	1.2	1.4	1.6	
С	0.60 TYP.			
D	7.00 BSC.			
D1	6.10	6.2	6.30	
е	2.54 BSC.			
E	5.00 BSC.			
E1	4.30	4.40	4.50	
L	1.07	1.27	1.47	
S		1.815 BSC.		
R		0.7 REF.		
aaa	—		0.15	
bbb	_		0.15	
CCC	ссс <u>—</u>		0.10	
ddd —		—	0.10	

Table 11. Package Diagram Dimensions (mm)



5. 6-Pin PCB Land Pattern

Figure 2 illustrates the 6-pin PCB land pattern for the Si550. Table 12 lists the values for the dimensions shown in the illustration.

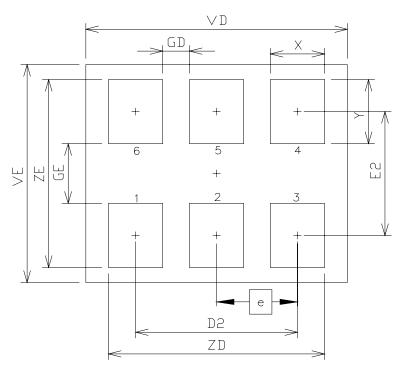


Figure 2. Si550 PCB Land Pattern

Table 12. PCB Land Pattern Dimensions (m	nm)
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Dimension	Min	Max		
D2	5.08 REF			
е	2.54 BSC			
E2	4.15 REF			
GD	0.84	—		
GE	2.00	—		
VD	8.20 REF			
VE	7	7.30 REF		
Х	X 1.70 TY			
Y	2.15 REF			
ZD	_	6.78		
ZE	_	6.30		
Notes				

Notes:

1. Dimensioning and tolerancing per the ANSI Y14.5M-1994 specification.

2. Land pattern design based on IPC-7351 guidelines.

3. All dimensions shown are at maximum material condition (MMC).

4. Controlling dimension is in millimeters (mm).



DOCUMENT CHANGE LIST

Revision 0.2 to Revision 0.3

- Updated 1. "Electrical Specifications" on page 2.
 - Updated ordering and format of Table 1 through Table 9.
 - Updated LVDS and CML in Table 4, "CLK± Output Levels and Symmetry," on page 3.
 - Updated RMS jitter values in Table 5, "CLK± Output Phase Jitter," on page 4.
 - Added Typical Phase Noise performance data in Table 5, "CLK± Output Phase Jitter," on page 4.
- Updated 3. "Ordering Information" on page 8.
 - Removed ordering option E at V_{DD} = 2.5 V in table for the 2nd Option Code.
 - Typical APRs replaced with minimum APR values.
 - New 135 ppm/V K_V option included.



CONTACT INFORMATION

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